

ABSTRACT

An operating method for a non-volatile memory device includes; performing a read operation on adjacent memory cells connected to an adjacent word line proximate to a target word line to determine adjacent data, classifying target memory cells connected to the target word line into groups according to the adjacent data, setting a read voltage level for each of the groups by searching for a read voltage level for target memory cells in at least one of the groups, and performing a read operation on target memory cells using the read voltage level set for each of the groups.

FIG. 1